

IN THE SPECIFICATION:

Please amend the paragraph beginning at line 6 of page 130 to read as follows:

--During (or before/after) the deposition of the desired silicon and electrical insulators in the active electronic portion 6504, the optical insulator materials are deposited in the an insulator strip 6906a and evanescent coupling gap region 6906b. In accordance with the present invention, evanescent coupling gap region 690b may be formed to include a tapered gap portion, or a uniformly shaped gap portion, and may comprise a thickness on the order of 0.5  $\mu$ m. Similarly, the etching of the silicon material for, and deposition of the desired material to form, the active electronic portion 6504 can occur simultaneously with the corresponding etching and deposition of the materials to form the passive optical portion 6506. The waveguide 6904 may additionally be considered as a passive optical portion.--